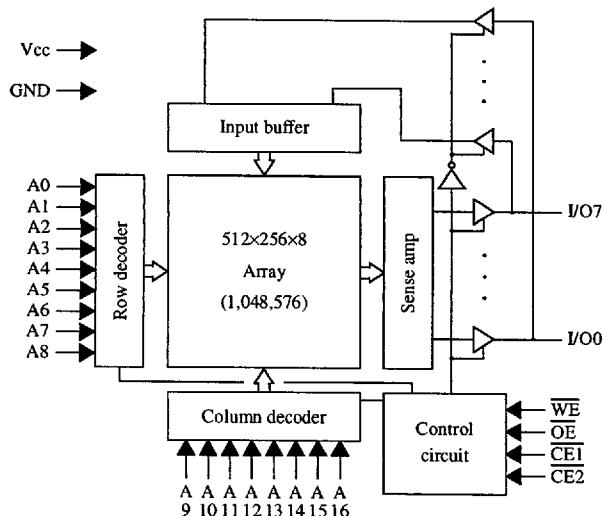


## Low voltage 128K×8 CMOS SRAM (Common I/O)

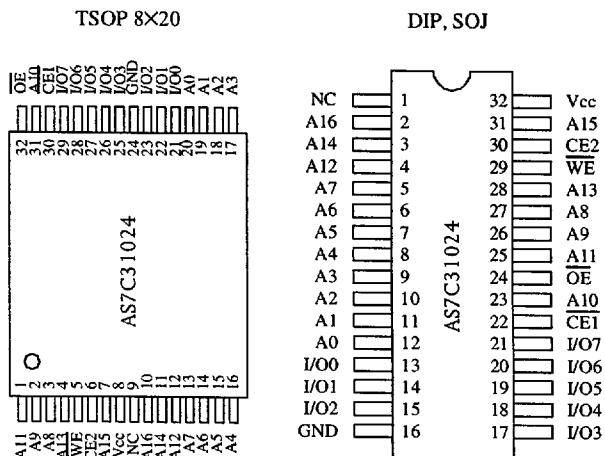
### Features

- Organization: 131,072 words × 8 bits
- Single 3.3 ±0.3V power supply
- 5V tolerant I/O specification
- High speed
  - 12/15/20/25/35 ns address access time
  - 3/4/5/6/8 ns output enable access time
- Very low power consumption
- Active: 270 mW max, (12 ns cycle)
- Standby: 18. mW max, CMOS I/O  
3.6 mW max, CMOS I/O, L version
- 2.0V data retention
- Equal access and cycle times
- Easy memory expansion with  $\overline{CE_1}$ ,  $CE_2$  and  $\overline{OE}$  inputs
- TTL-compatible, three-state I/O
- Ideal for cache, modem, portable computing
  - 75% power reduction during CPU idle mode
- 32-pin JEDEC standard packages
  - 300 mil PDIP and SOJ
  - 8 × 20 TSOP
- ESD protection >2000 volts
- Latch-up current >200 mA

### Logic block diagram



### Pin arrangement



### Selection guide

	7C31024-12	7C31024-15	7C31024-20	7C31024-25	7C31024-35	Unit
Maximum address access time	1.2	15	20	25	35	ns
Maximum output enable access time	3	4	5	6	8	ns
Maximum operating current	75	70	65	60	55	mA
Maximum CMOS standby current	5.0	5.0	5.0	5.0	5.0	mA
L	1.0	1.0	1.0	1.0	1.0	mA

Shaded areas contain advance information.



## Functional description

The AS7C31024 is a 3.3V high performance CMOS 1,048,576-bit Static Random Access Memory (SRAM) organized as 131,072 words  $\times$  8 bits. It is designed for memory applications requiring fast data access at low voltage, including Pentium<sup>TM</sup>, PowerPC<sup>TM</sup>, and portable computing. Alliance's advanced circuit design and process techniques permit 3.3V operation without sacrificing performance or operating margins.

The device enters standby mode when  $\overline{\text{CE1}}$  is HIGH or  $\overline{\text{CE2}}$  is LOW. CMOS standby mode consumes  $\leq 18$ . mW ( $\leq 3.6$ mW for the L version). Normal operation offers 75% power reduction after initial access, resulting in significant power savings during CPU idle, suspend, and stretch mode. Both versions of the AS7C31024 offer 2.0V data retention.

Equal address access and cycle times ( $t_{AA}$ ,  $t_{RC}$ ,  $t_{WC}$ ) of 12/15/20/25/35 ns with output enable access times ( $t_{OE}$ ) of 3/4/5/6/8 ns are ideal for high performance applications. The active high and low chip enables ( $\overline{\text{CE1}}$ ,  $\overline{\text{CE2}}$ ) permit easy memory expansion with multiple-bank memory systems.

A write cycle is accomplished by asserting write enable ( $\overline{\text{WE}}$ ) and both chip enables ( $\overline{\text{CE1}}$ ,  $\overline{\text{CE2}}$ ). Data on the input pins I/O0-I/O7 is written on the rising edge of  $\overline{\text{WE}}$  (write cycle 1) or the active-to-inactive edge of  $\overline{\text{CE1}}$  or  $\overline{\text{CE2}}$  (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable (OE) or write enable (WE).

A read cycle is accomplished by asserting output enable (OE) and both chip enables ( $\overline{\text{CE1}}$ ,  $\overline{\text{CE2}}$ ), with write enable ( $\overline{\text{WE}}$ ) HIGH. The chip drives I/O pins with the data word referenced by the input address. When either chip enable or output enable is inactive, or write enable is active, output drivers stay in high-impedance mode.

All chip inputs and outputs are TTL-compatible, and 5V tolerant. Operation is from a single  $3.3 \pm 0.3$ V supply. The AS7C31024 is packaged in all high volume industry standard packages.

## Absolute maximum ratings

Parameter	Symbol	Min	Max	Unit
Power supply voltage relative to GND	$V_{CC}$	-0.5	+4.6	V
Input voltage relative to GND	$V_{IN}$	-0.5	+6.0	V
Power dissipation	$P_D$	-	1.0	W
Storage temperature (plastic)	$T_{stg}$	-55	+150	°C
Temperature under bias	$T_{bias}$	-10	+85	°C
DC output current	$I_{out}$	-	20	mA

Stresses greater than those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

## Truth table

$\overline{\text{CE1}}$	$\overline{\text{CE2}}$	$\overline{\text{WE}}$	$\overline{\text{OE}}$	Data	Mode
H	X	X	X	High Z	Standby ( $I_{SB}$ , $I_{SB1}$ )
X	L	X	X	High Z	Standby ( $I_{SB}$ , $I_{SB1}$ )
L	H	H	H	High Z	Output disable
L	H	H	L	$D_{out}$	Read
L	H	L	X	$D_{in}$	Write

Key: X = Don't Care, L = LOW, H = HIGH



## Recommended operating conditions

 $T_a = 0^\circ\text{C}$  to  $+70^\circ\text{C}$ 

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V <sub>CC</sub>	3.0	3.3	3.6	V
	GND	0.0	0.0	0.0	V
Input voltage	V <sub>IH</sub>	2.0	—	5.5	V
	V <sub>IL</sub>	-0.5 <sup>†</sup>	—	0.8	V

<sup>†</sup>V<sub>IL</sub> min = -2.0V for pulse width less than t<sub>RC</sub>/2.DC operating characteristics<sup>1</sup>V<sub>CC</sub> = 3.3 ± 0.3V, GND = 0V, T<sub>a</sub> = 0°C to +70°C

Parameter	Symbol	Test Conditions	12		-15		-20		-25		-35		Unit
			Min	Max									
Input leakage current	I <sub>LI</sub>	V <sub>CC</sub> = Max, V <sub>in</sub> = GND to V <sub>CC</sub>	—	1	—	1	—	1	—	1	—	1	μA
Output leakage current	I <sub>LO</sub>	CE1 = V <sub>IH</sub> or CE2 = V <sub>IL</sub> , V <sub>CC</sub> = Max, V <sub>out</sub> = GND to V <sub>CC</sub>	—	1	—	1	—	1	—	1	—	1	μA
Operating power supply current	I <sub>CC</sub>	CE1 = V <sub>IL</sub> , CE2 = V <sub>IH</sub> , f = f <sub>max</sub> , I <sub>out</sub> = 0 mA	—	75	—	70	—	65	—	60	—	55	mA
Standby power supply current	I <sub>SB</sub>	CE1 = V <sub>IH</sub> or CE2 = V <sub>IL</sub> , f = f <sub>max</sub>	—	3.5	—	3.0	—	2.5	—	2.5	—	2.0	mA
	I <sub>SB1</sub>	CE1 ≥ V <sub>CC</sub> - 0.2V or CE2 ≤ 0.2V, V <sub>in</sub> ≤ 0.2V or V <sub>in</sub> ≥ V <sub>CC</sub> - 0.2V, f = 0	—	5.0	—	5.0	—	5.0	—	5.0	—	5.0	mA
Output voltage	V <sub>OL</sub>	I <sub>OL</sub> = 8 mA, V <sub>CC</sub> = Min	—	0.4	—	0.4	—	0.4	—	0.4	—	0.4	V
	V <sub>OH</sub>	I <sub>OH</sub> = -4 mA, V <sub>CC</sub> = Min	2.4	—	2.4	—	2.4	—	2.4	—	2.4	—	V

Capacitance<sup>2</sup>f = 1 MHz, T<sub>a</sub> = Room temperature, V<sub>CC</sub> = 3.3V

Parameter	Symbol	Signals	Test Conditions	Max	Unit
Input capacitance	C <sub>IN</sub>	A, CE1, CE2, WE, OE	V <sub>in</sub> = 0V	5	pF
I/O capacitance	C <sub>I/O</sub>	I/O	V <sub>in</sub> = V <sub>out</sub> = 0V	7	pF

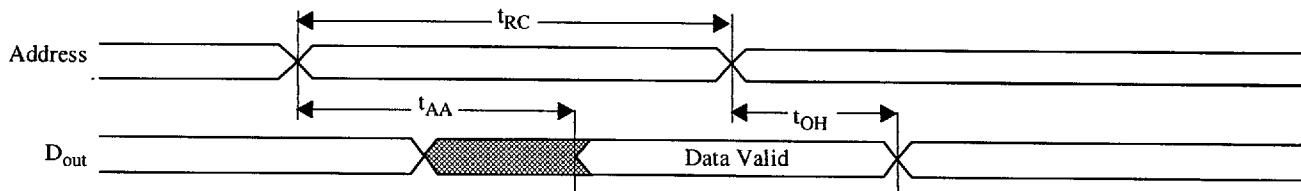
Read cycle<sup>3,9,12</sup>(V<sub>CC</sub> = 3.3±0.3V, GND = 0V, T<sub>a</sub> = 0°C to +70°C)

Parameter	Symbol	-12		-15		-20		-25		-35		Unit	Notes
		Min	Max										
Read cycle time	t <sub>RC</sub>	1.2	—	15	—	20	—	25	—	35	—	ns	
Address access time	t <sub>AA</sub>	—	1	—	15	—	20	—	25	—	35	ns	3
Chip enable (CE1) access time	t <sub>ACE1</sub>	—	12	—	15	—	20	—	25	—	35	ns	3, 12
Chip enable (CE2) access time	t <sub>ACE2</sub>	—	12	—	15	—	20	—	25	—	35	ns	3, 12
Output enable (OE) access time	t <sub>OE</sub>	—	3	—	4	—	5	—	6	—	8	ns	
Output Hold from address change	t <sub>OH</sub>	—	3	—	3	—	3	—	3	—	3	ns	5
CE1 LOW to output in Low Z	t <sub>CLZ1</sub>	—	3	—	3	—	3	—	3	—	3	ns	4, 5, 12
CE2 HIGH to output in Low Z	t <sub>CLZ2</sub>	—	3	—	3	—	3	—	3	—	3	ns	4, 5, 12
CE1 HIGH to output in High Z	t <sub>CHZ1</sub>	—	3	—	4	—	5	—	6	—	8	ns	4, 5, 12
CE2 LOW to output in High Z	t <sub>CHZ2</sub>	—	3	—	4	—	5	—	6	—	8	ns	4, 5, 12
OE LOW to output in Low Z	t <sub>OLZ</sub>	—	0	—	0	—	0	—	0	—	0	ns	4, 5
OE HIGH to output in High Z	t <sub>OHZ</sub>	—	3	—	4	—	5	—	6	—	8	ns	4, 5
Power up time	t <sub>PU</sub>	—	0	—	0	—	0	—	0	—	0	ns	4, 5, 12
Power down time	t <sub>PD</sub>	—	12	—	15	—	20	—	25	—	35	ns	4, 5, 12

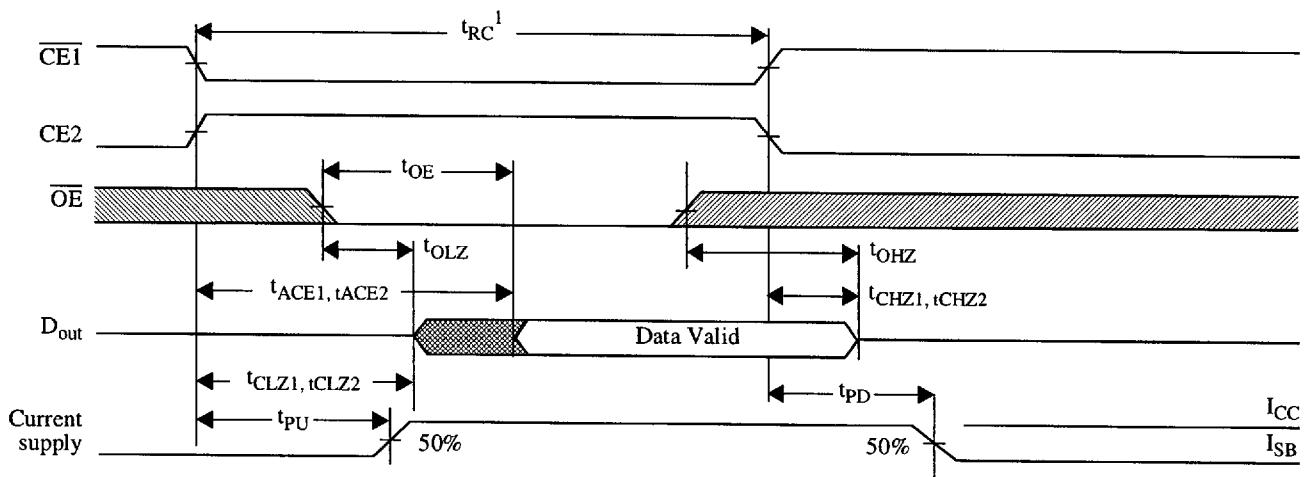
Shaded areas contain advance information.

Read waveform 1<sup>3,6,7,9,12</sup>

Address controlled

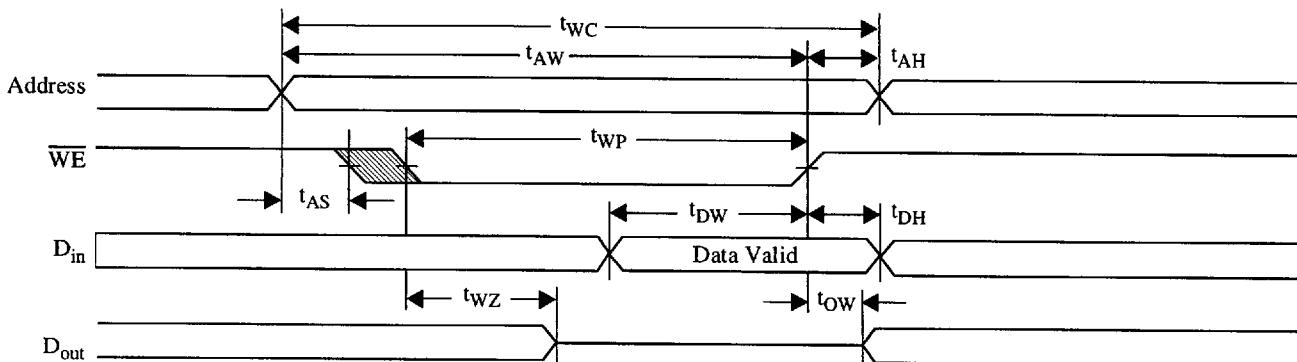
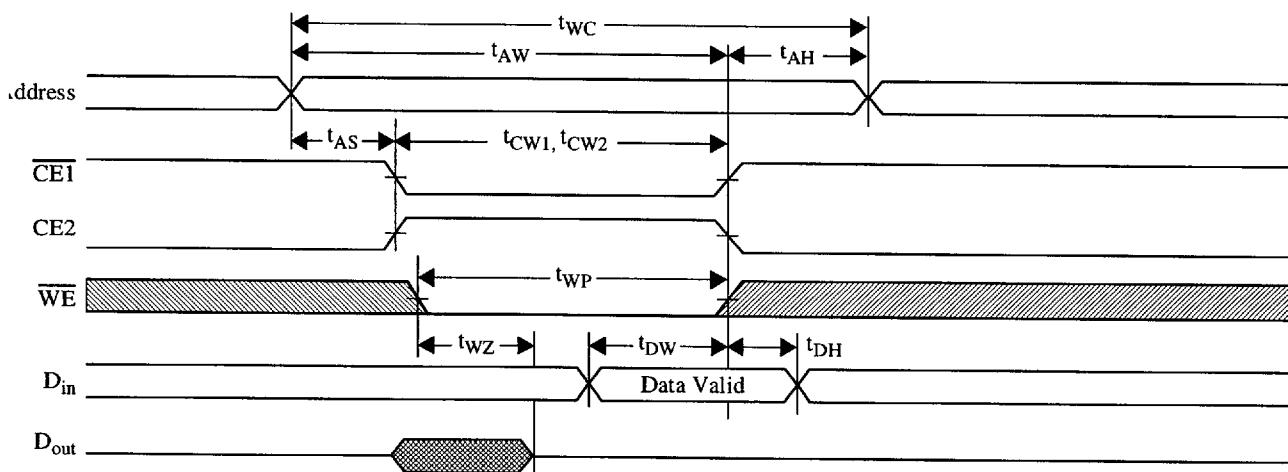
Read waveform 2<sup>3,6,8,9,12</sup>

CE1 and CE2 controlled



Write cycle<sup>11,12</sup>(V<sub>CC</sub> = 3.3±0.3V, GND = 0V, Ta = 0°C to +70°C)

Parameter	Symbol	-12		-15		-20		-25		-35		Unit	Notes
		Min	Max										
Write cycle Time	t <sub>WC</sub>	12	—	15	—	20	—	20	—	30	—	ns	
Chip enable ( $\overline{CE1}$ ) to write end	t <sub>CW1</sub>	10	—	12	—	12	—	15	—	20	—	ns	12
Chip enable ( $CE2$ ) to write end	t <sub>CW2</sub>	10	—	12	—	12	—	15	—	20	—	ns	12
Address setup to write end	t <sub>AW</sub>	10	—	12	—	12	—	15	—	20	—	ns	
Address setup time	t <sub>AS</sub>	0	—	0	—	0	—	0	—	0	—	ns	12
Write pulse width	t <sub>WP</sub>	8	—	9	—	12	—	15	—	17	—	ns	
Address hold from end of write	t <sub>AH</sub>	0	—	0	—	0	—	0	—	0	—	ns	
Data valid to write end	t <sub>DW</sub>	6	—	8	—	10	—	12	—	15	—	ns	
Data hold time	t <sub>DH</sub>	0	—	0	—	0	—	0	—	0	—	ns	4, 5
Write enable to output in High Z	t <sub>WZ</sub>	—	5	—	5	—	5	—	5	—	5	ns	4, 5
Output active from write end	t <sub>OW</sub>	3	—	3	—	3	—	3	—	3	—	ns	4, 5

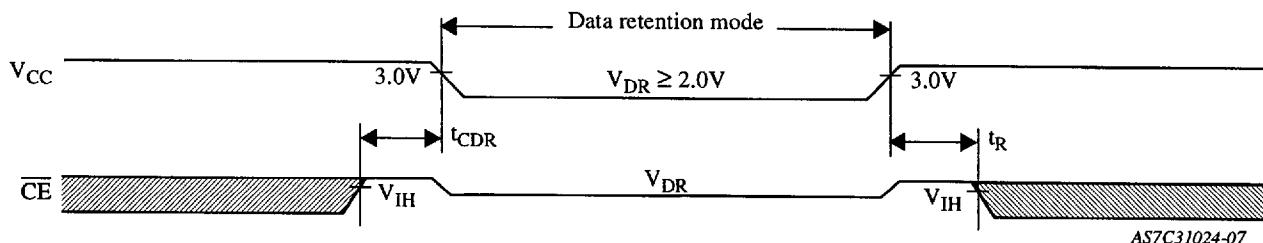
Write waveform 1<sup>10,11,12</sup> $\overline{WE}$  controlledWrite waveform 2<sup>10,11,12</sup> $\overline{CE1}$  and  $CE2$  controlled



## Data retention characteristics

Parameter	Symbol	Test Conditions	Min	Max	Unit
V <sub>CC</sub> for data retention	V <sub>DR</sub>	V <sub>CC</sub> = 2.0V	2.0	—	V
Data retention current	I <sub>CCDR</sub>	$\overline{CE1} \geq V_{CC} - 0.2V$ or $CE2 \leq 0.2V$	—	2500	μA
Chip enable to data retention time	t <sub>CDR</sub>	—	—	500	μA
Operation recovery time	t <sub>R</sub>	$V_{in} \geq V_{CC} - 0.2V$ or $V_{in} \leq 0.2V$	t <sub>RC</sub>	—	ns
Input leakage current	I <sub>LI</sub>	—	—	1	μA

## Data retention waveform



AS7C31024-07

## AC test conditions

- Output load: see Figure B,  
except for t<sub>CLZ</sub> and t<sub>CHZ</sub> see Figure C.
- Input pulse level: GND to 3.0V. See Figure A.
- Input rise and fall times: 5 ns. See Figure A.
- Input and output timing reference levels: 1.5V.

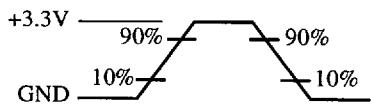


Figure A: Input waveform

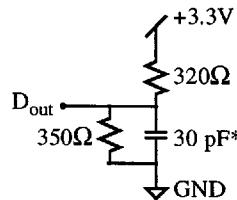
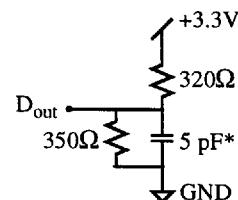
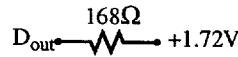


Figure B: Output load

Thevenin equivalent:

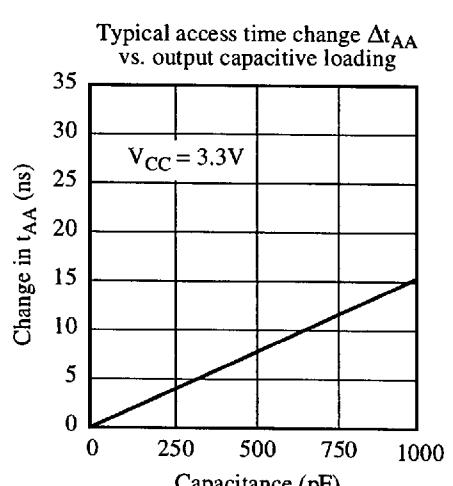
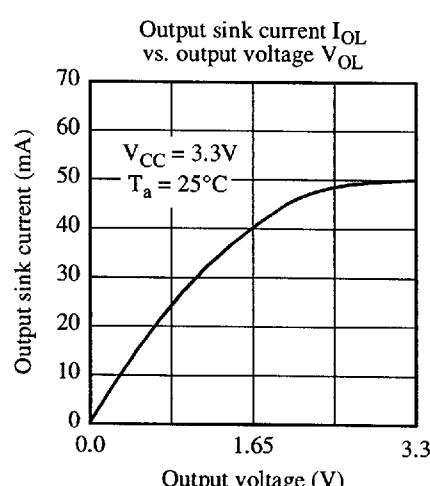
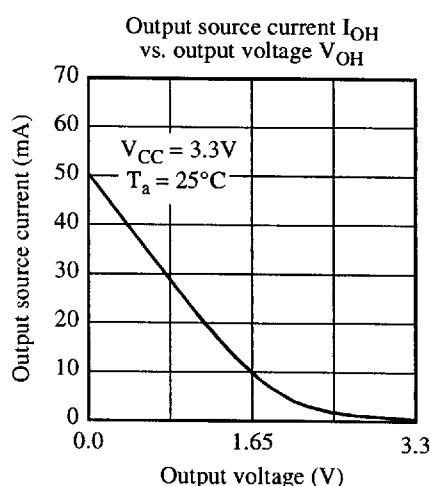
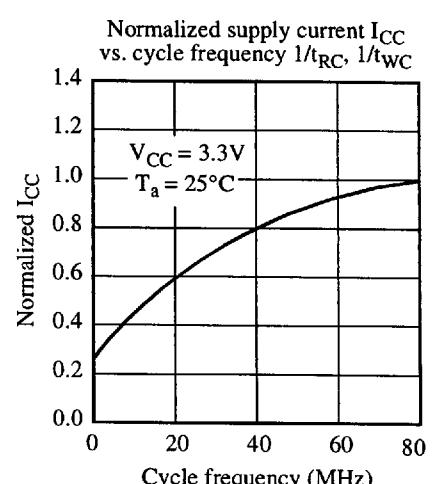
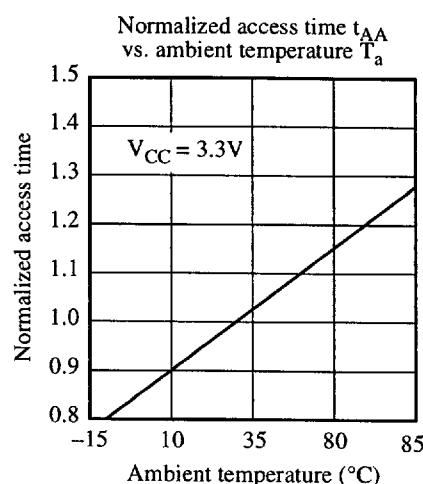
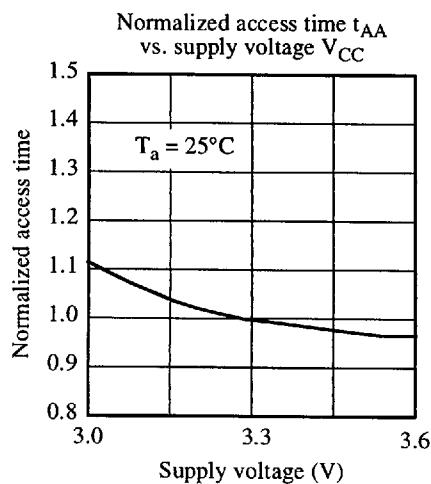
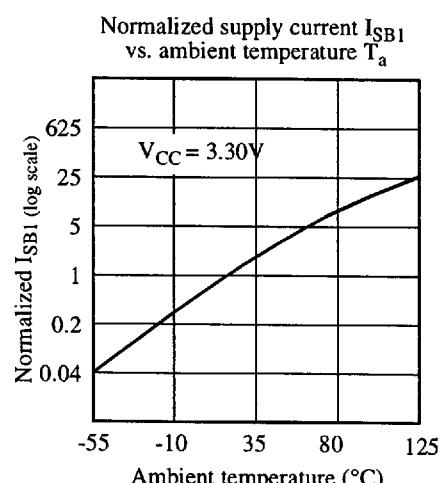
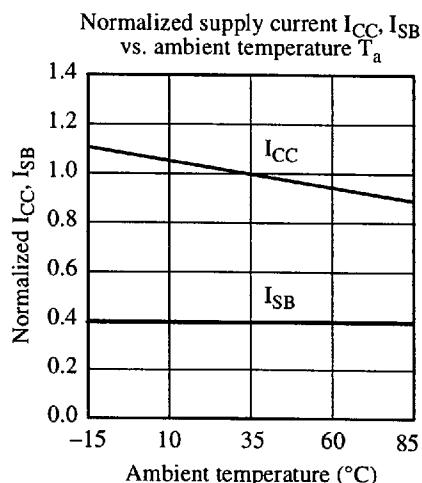
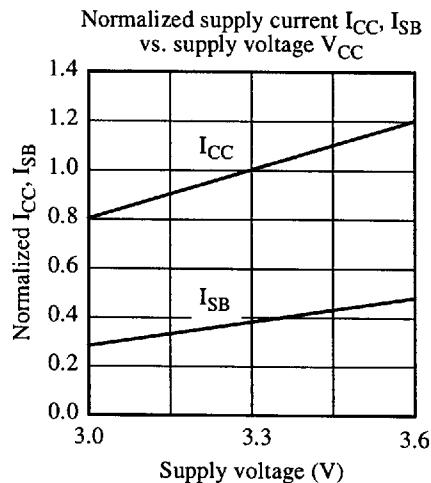
\*including scope  
and jig capacitanceFigure C: Output load for t<sub>CLZ</sub>, t<sub>CHZ</sub>

## Notes

- 1 During V<sub>CC</sub> power-up, a pull-up resistor to V<sub>CC</sub> on  $\overline{CE1}$  is required to meet I<sub>SB</sub> specification.
- 2 This parameter is sampled and not 100% tested.
- 3 For test conditions, see AC Test Conditions, Figures A, B, C.
- 4 t<sub>CLZ</sub> and t<sub>CHZ</sub> are specified with CL = 5pF as in Figure C. Transition is measured  $\pm 500\text{mV}$  from steady-state voltage.
- 5 This parameter is guaranteed but not tested.
- 6  $\overline{WE}$  is HIGH for read cycle.
- 7  $\overline{CE1}$  and  $\overline{OE}$  are LOW and  $CE2$  is HIGH for read cycle.
- 8 Address valid prior to or coincident with  $\overline{CE}$  transition LOW.
- 9 All read cycle timings are referenced from the last valid address to the first transitioning address.
- 10  $\overline{CE1}$  or  $\overline{WE}$  must be HIGH or  $CE2$  LOW during address transitions.
- 11 All write cycle timings are referenced from the last valid address to the first transitioning address.
- 12  $\overline{CE1}$  and  $CE2$  have identical timing.



## Typical DC and AC characteristics





## Ordering information

Package \ Access Time	12 ns	15 ns	20 ns	25 ns	35 ns
Plastic DIP, 300 mil	AS7C31024-12PC AS7C31024L-12PC	AS7C31024-15PC AS7C31024L-15PC	AS7C31024-20PC AS7C31024L-20PC	AS7C31024-25PC AS7C31024L-25PC	AS7C31024-35PC AS7C31024L-35PC
Plastic SOJ, 300 mil	AS7C31024-12JC AS7C31024L-12JC	AS7C31024-15JC AS7C31024L-15JC	AS7C31024-20JC AS7C31024L-20JC	AS7C31024-25JC AS7C31024L-25JC	AS7C31024-35JC AS7C31024L-35JC
TSOP 8x20	AS7C31024-12TC AS7C31024L-12TC	AS7C31024-15TC AS7C31024L-15TC	AS7C31024-20TC AS7C31024L-20TC	AS7C31024-25TC AS7C31024L-25TC	AS7C31024-35TC AS7C31024L-35TC

## Part numbering system

AS7C	3	1024	-XX	X	C
SRAM prefix	Blank	= 5V supply	Device	Package:	P = PDIP 300 mil
<b>DOMESTIC REPS</b>	3	= 3.3V supply	number	J = SOJ 300 mil	Commercial temperature
ALABAMA	KANSAS	ConTech	NEW JERSEY	T = TSOP 8x20	range, 0°C to 70°C
Concord Component (205) 772-8883	(816) 358-8100	North	TENNESSEE	FM KOREA	+822-596-3880 fm@knet.co.kr
KENTUCKY	(317) 921-3000	ERA Associates (800) 645-5500	Concord Component	Ottawa (613) 592-9540	Woo Young Tech +822-369-7099
Representatives, distributors, and sales offices	Southern States Marketing (214) 238-7500	Electro Tech (610) 272-2125	Austin (512) 835-5822	Toronto (905) 672-2030	MALAYSIA Exer Technologies +60-4-657-9592
CALIFORNIA	LOUISIANA	NEW YORK	Dallas (214) 238-7500	Dallas (514) 747-1211	PUERTO RICO Micro-Electronic Comp. (787) 746-9897
North	Southern States Marketing	NYC	Houston (713) 895-8533	Vancouver (604) 473-4666	SINGAPORE Exer Technologies +65-749-1349
Brooks Technical (415) 960-3880	North	ERA Associates (516) 543-0510	UTAH	Calgary (403) 291-6755	TAIWAN Asian Specific Tech. +886-2-521-2363
LA Area	South	Upstate	Charles Fields & Assoc. (801) 299-8228	EUROPE	Golden Way Electronics +886-2-698-1868 x505
Competitive Tech. (714) 450-0170	LOUISIANA	Tri-Tech	Rochester (716) 385-6500	Britcomp Sales Surrey, England +44-1932 347077 +44-1932 346256	Puteam International +886-2-719-0373
San Diego	MAINE	NEW YORK	Binghamton (607) 722-3580	MUNICH, Germany +49-894488496	DISTRIBUTORS
ATS (619) 634-1488	Kitchen & Kutchin (617) 229-2660	NYC	NORTH CAROLINA	Athismons, France +33-1-69387678	All American HQ: (305) 621-8282
COLORADO	MARYLAND	ERA Associates (516) 543-0510	Concord Component (919) 846-3441	WEST VIRGINIA	Axis Components, Inc. HQ: (800) 536-0225
Technology Sales (303) 692-5835	Chesapeake Tech. (301) 236-0530	Upstate	Charles Fields & Assoc. (801) 299-8228	interACTIVE Great Britain, Ireland +44-1773-740263	Future Electronics HQ: (514) 594-7710
CONNECTICUT	MASSACHUSETTS	Tri-Tech	Rochester (716) 385-6500	WISCONSIN	Interface Electronics HQ: (800) 632-7792
Kitchen & Kutchin (203) 239-0212	Kitchen & Kutchin (617) 229-2660	ROCHESTER	Binghamton (607) 722-3580	D. A. Case Associates (612) 831-6777	Please contact your rep to locate a distributor near you
DELAWARE	MICHIGAN	NEW YORK	NORTH CAROLINA	Dayton (513) 433-2511	AUSTRIA
Electro Tech (610) 272-2125	Enco Group (810) 338-8600	NEW YORK	Concord Component (919) 846-3441	Dayton (513) 433-2511	Great Britain, Ireland +44-1773-740263
FLORIDA	MINNESOTA	NEW YORK	NORTH DAKOTA	Dayton (513) 433-2511	WISCONSIN
Micro-Electronic Comp. Deerfield Beach (954) 426-8944	D. A. Case Associates (612) 831-6777	NEW YORK	D. A. Case Associates (612) 831-6777	Dayton (513) 433-2511	D. A. Case Associates (612) 831-6777
Orlando (407) 682-9602	MISSOURI	NEW YORK	NORTH DAKOTA	Dayton (513) 433-2511	WYOMING
Tampa (813) 393-5011	CenTech	NEW YORK	D. A. Case Associates (612) 831-6777	Dayton (513) 433-2511	Technology Sales (303) 692-8835
GEORGIA	MICHIGAN	NEW YORK	ES/Chase (503) 684-8500	Dayton (513) 433-2511	INTERNATIONAL REPS
Concord Component (770) 416-9597	Enco Group (810) 338-8600	NEW YORK	ES/Chase (503) 684-8500	Dingley R&D Electronics +61-3-9558-0444	AUSTRALIA
HAWAII	MISSISSIPPI	NEW YORK	ES/Chase (503) 684-8500	Bayswater ACD +61-3-9762-7644	INDIA
Brooks Technical (415) 960-3880	Concord Component (205) 772-8883	NEW YORK	ES/Chase (503) 684-8500	Dayton (513) 433-2511	Priya Electronics, Inc. San Jose, CA USA (408) 954-1866
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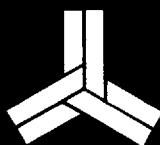
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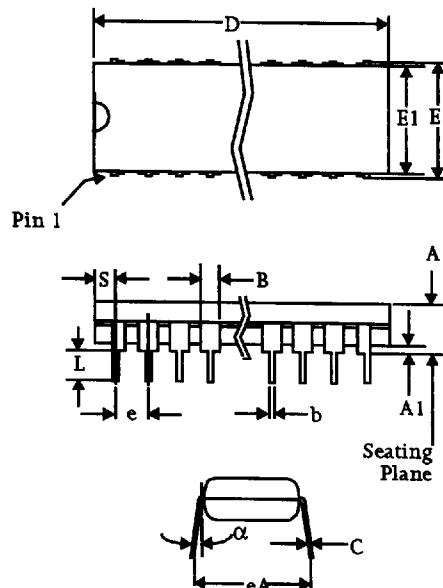


## Package diagrams

## Plastic dual in-line package (PDIP)

	20-pin 300 mil		28-pin 300 mil		32-pin 300 mil		32-pin 400 mil	
	Min	Max	Min	Max	Min	Max	Min	Max
A	-	0.175	-	0.175	-	0.180	-	0.200
A1	0.010	-	0.010	-	0.015	-	0.015	-
B	0.046	0.054	0.058	0.064	0.045	0.055	0.045	0.065
b	0.018	0.024	0.016	0.022	0.015	0.021	0.014	0.022
C	0.008	0.014	0.008	0.014	0.008	0.012	0.009	0.015
D	-	0.980	-	1.400	-	1.571	-	1.620
E	0.290	0.310	0.295	0.320	0.300	0.325	0.390	0.425
E1	0.263	0.293	0.278	0.298	0.280	0.295	0.340	0.390
e	0.100 BSC		0.100 BSC		0.100 BSC		0.100 BSC	
eA	0.310	0.350	0.330	0.370	0.330	0.370	0.430	0.470
L	0.110	0.130	0.120	0.140	0.110	0.142	0.118	0.162
$\alpha$	0°	15°	0°	15°	0°	15°	0°	15°
S	-	0.040	-	0.055	-	0.043	-	0.065

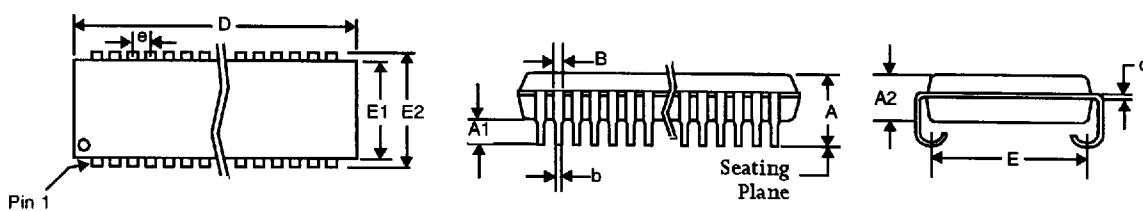
Dimensions in inches



## Plastic small outline J-bend (SOJ)

	20/26-pin 300 mil		28-pin 300 mil		32-pin 300 mil		28-pin 400 mil		32-pin 400 mil		36-pin 400 mil		40-pin 400 mil		42-pin 400 mil		44-pin 400 mil		
	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
A	-	0.140	-	0.140	-	0.145	0.132	0.146	-	0.145	-	-	-	0.145	0.128	0.148	0.128	0.148	
A1	0.020	-	0.025	-	0.025	-	0.062	-	0.025	-	-	-	0.025	-	0.025	-	0.025	-	
A2	0.095	0.105	0.095	0.105	0.086	0.105	0.105	115	0.086	0.115	0.102 NOM	0.086	0.115	1.105	1.115	1.105	1.115		
B	0.025	0.032	0.028 TYP		0.026	0.032	0.024	0.032	0.026	0.032	-	0.032	0.026	0.032	0.026	0.032	0.026	0.032	
b	0.016	0.022	0.018 TYP		0.014	0.020	0.013	0.021	0.015	0.020	0.013	0.021	0.015	0.022	0.015	0.020	0.015	0.020	
c	0.008	0.014	0.010 TYP		0.006	0.013	0.005	0.012	0.007	0.013	-	-	0.007	0.014	0.007	0.013	0.007	0.013	
D	-	0.686	-	0.730	0.820	0.830	0.720	0.729	0.820	0.830	0.920	0.930	1.015	1.035	1.070	1.080	1.120	1.130	
E	0.327	0.347	0.327	0.347	0.330	0.340	0.430	0.440	0.435	0.445	0.350	0.390	0.435	0.445	0.370 NOM	0.370 NOM			
E1	0.295	0.305	0.295	0.305	0.292	0.305	0.395	0.405	0.395	0.405	0.400 NOM	0.395	0.405	0.395	0.405	0.395	0.405		
E2	0.245	0.285	0.245	0.285	0.250	0.275	0.354	0.378	0.360	0.380	0.435	0.445	0.348	0.390	0.435	0.445	0.435	0.445	
e	0.050 BSC		0.050 BSC		0.050 BSC		0.050 BSC		0.050 BSC		0.045	0.055	0.050 BSC		0.050 NOM		0.050 NOM		

Dimensions in inches



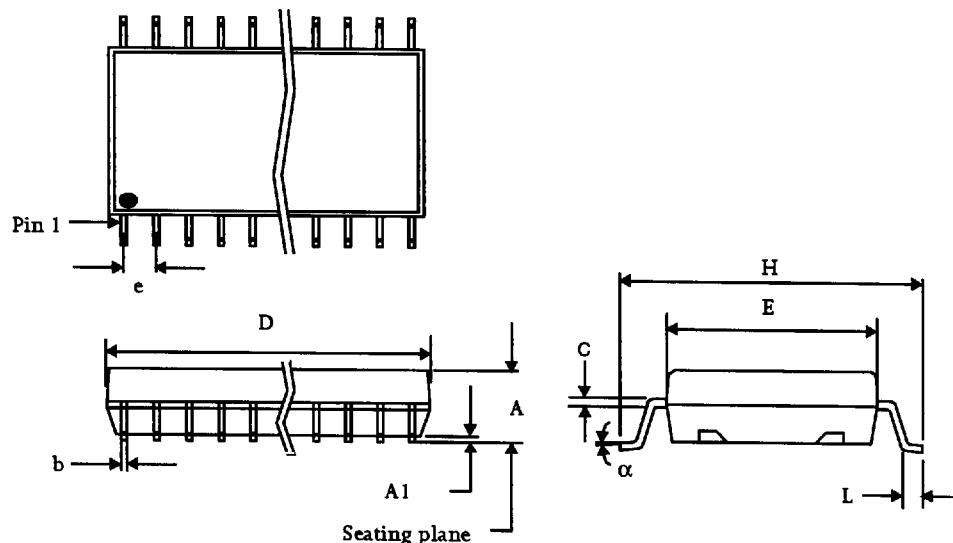
## Package diagrams



Plastic small outline gull wing IC (SOIC)

28-pin 330 mil	
	Min      Max
A	-      0.112
A1	0.004      -
b	0.014      0.020
C	0.008      0.014
D	-      0.733
e	0.050 nominal
E	0.326      0.336
H	0.453      0.477
L	0.028      0.044
$\alpha$	0°      10°

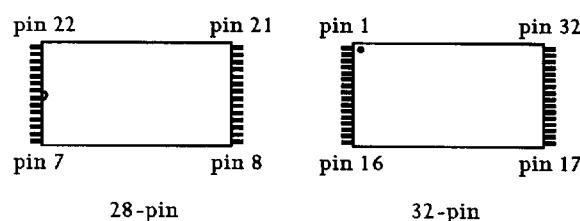
Dimensions in inches



Thin small outline package (TSOP-I)

28-pin 8×13.4		32-pin 8×20		40-pin 10×20	
Min	Max	Min	Max	Min	Max
A	-	1.20	-	1.20	-
A1	0.05	0.15	0.05	0.15	0.05
A2	0.90	1.05	0.90	1.05	0.95
b	0.17	0.27	0.17	0.23	0.17
C	0.10	-	0.10	-	0.10
D	11.70	11.90	18.20	18.60	18.30
e	0.55 nominal		0.50 nominal		0.50 nominal
E	8.0 nominal		7.80	8.20	9.90
Hd	13.20	13.60	19.80	20.20	19.80
L	0.30	0.70	0.40	0.60	0.50
$\alpha$	0°	5°	1°	5°	0°

Dimensions in millimeters



28-pin                          32-pin

